

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

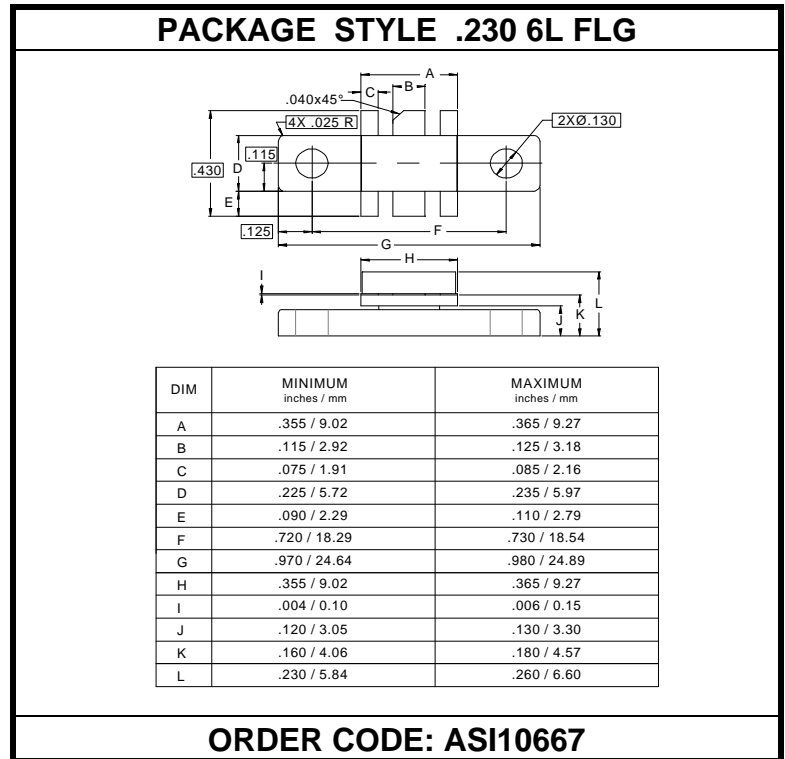
The **ASI UHBM45** is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	9.0 A
V_{CB0}	36 V
V_{CEO}	18 V
V_{CES}	36 V
V_{EBO}	4.0 V
P_{DISS}	150 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.2 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 50 mA	36			V
BV_{CES}	I _C = 50 mA R _{BE} = 10 Ω	18			V
BV_{EBO}	I _E = 10 mA	4.0			V
I_{CB0}	V _{CB} = 15 V			5	mA
h_{FE}	V _{CE} = 5.0 V I _C = 1.0 A	5		200	---
C_{OB}	V _{CB} = 12.5 V f = 1.0 MHz		80		pF
P_G η_C	V _{CE} = 12.5 V P _{OUT} = 45 W f = 836 MHz	4.7	35		dB %